

IN THE CLAIMS:

1. (Currently Amended) A method for manufacturing a semiconductor device, comprising:

forming a polysilicon gate electrode over a substrate;

forming source/drain regions in said substrate proximate said polysilicon gate electrode;

forming a blocking layer over said source/drain regions in a step, said blocking layer comprising a metal silicide;

siliciding said polysilicon gate electrode to form a silicided gate electrode in a later step, said blocking layer protecting said source/drain regions from said siliciding.

Claim 2 (Canceled)

3. (Original) The method as recited in Claim 1 wherein said blocking layer is a silicided source/drain contact region.

4. (Original) The method as recited in Claim 1 wherein said silicided gate electrode comprises a different metal silicide than said blocking layer.

5. (Original) The method as recited in Claim 4 wherein said blocking layer comprises a cobalt silicide and said silicided gate electrode comprises a nickel silicide.

6. (Original) The method as recited in Claim 1 wherein said blocking layer has a thickness ranging from about 10 nm to about 35 nm.

7. (Original) The method as recited in Claim 1 further including forming a protective layer over said polysilicon gate electrode prior to said forming a blocking layer over said source/drain regions.

8. (Original) The method as recited in Claim 7 wherein said protective layer is a silicon nitride protective layer.

9. (Original) The method as recited in Claim 1 wherein siliciding said polysilicon gate electrode to form a silicided gate electrode includes fully siliciding said polysilicon gate electrode to form a fully silicided gate electrode.

10. (Currently Amended) A method for manufacturing an integrated circuit, comprising:

forming semiconductor devices over a substrate, including;

forming a polysilicon gate electrode over a substrate;

forming source/drain regions in said substrate proximate said polysilicon gate electrode;

forming a blocking layer over said source/drain regions in a step, said blocking layer comprising a metal silicide;

siliciding said polysilicon gate electrode to form a silicided gate electrode in a later step, said blocking layer protecting said source/drain regions from said siliciding; and

forming interconnects within dielectric layers located over said substrate for electrically contacting said semiconductor devices.

Claim 11 (Canceled)

12. (Original) The method as recited in Claim 10 wherein said blocking layer is a silicided source/drain contact region.

13. (Original) The method as recited in Claim 10 wherein said silicided gate electrode comprises a different metal silicide than said blocking layer.

14. (Original) The method as recited in Claim 13 wherein said blocking layer comprises a cobalt silicide and said silicided gate electrode comprises a nickel silicide.

15. (Original) The method as recited in Claim 10 wherein said blocking layer has a thickness ranging from about 10 nm to about 35 nm.

16. (Original) The method as recited in Claim 10 further including forming a protective layer over said polysilicon gate electrode prior to said forming a blocking layer over said source/drain regions.

17. (Original) The method as recited in Claim 16 wherein said protective layer is a silicon nitride protective layer.

18. (Original) The method as recited in Claim 10 wherein siliciding said polysilicon gate electrode to form a silicided gate electrode includes fully siliciding said polysilicon gate electrode to form a fully silicided gate electrode.

19. (Previously Presented) The method as recited in Claim 1 wherein siliciding said polysilicon gate electrode to form said silicided gate electrode occurs prior to siliciding any portion of the polysilicon gate electrode.

20. (Currently Amended) The method as recited in ~~Claim 11~~Claim 10 wherein siliciding said polysilicon gate electrode to form said silicided gate electrode occurs prior to siliciding any portion of the polysilicon gate electrode.